

09/164216

PATENT

ABSTRACT

5 A semiconductor chip is ESD protected, in part,  
by utilizing floating lateral clamp diodes. Unlike  
conventional clamp diodes, which are based upon  
parasitic bipolar devices associated with large MOS  
transistors, the floating lateral clamp diodes  
utilize a well formed in the substrate as the  
cathode, and a plurality of regions of the opposite  
10 conductivity type which are formed in the well as the  
anode.